

# Slide Supplement



## A Subnanosecond 0.5 $\mu$ m 64b Adder

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A subnanosecond 64b adder implementation in 0.5 $\mu$ m CMOS forms the basis for integer and floating-point units of a microprocessor. Integrating dual-rail dynamic logic and Ling's equations, the adder contains 7k transistors in 0.246mm<sup>2</sup>. It executes a full 64b add and latches the result in under 1ns at nominal conditions.

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## Motivation

**Why are designers always working on faster adders?**

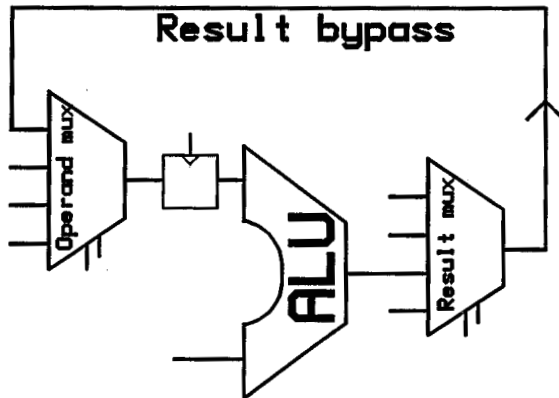
**Adders occupy the critical path in many key areas of microprocessor operation**

- Arithmetic Logic Units
- Memory address generation
- Floating point calculations

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## Motivation: ALU

ALU operation in a typical CPU

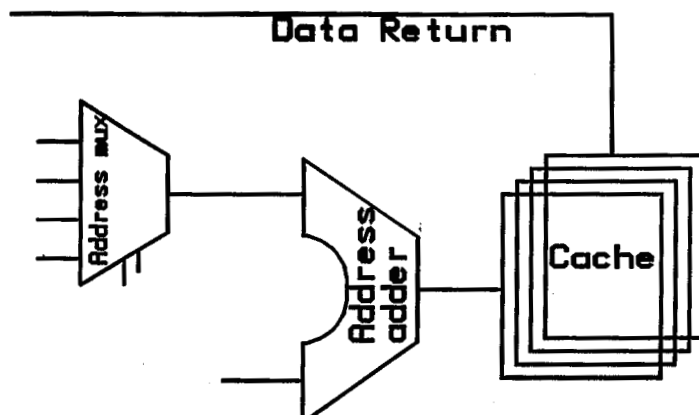


Operand to result bypass is often the cycle time limiter  
☞ A fast ALU (adder) is essential

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## Motivation: Address Add

Time from address selection to cache data return will often be the chip frequency limiter. The address adder occupies a significant portion of this budget.



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## Motivation: FPU

Adders occupy numerous critical paths in an FMAC.

- Generation of the 3X multiple for the Booth re-coded multiplier array
- Summation of the carry-save multiplier results (112 bit addition required here)
- Final IEEE rounding increment

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## Design Goals for the PA8000 Adder Given that:

- ◆ Over 20 Adders are used on the processor
- ◆ Many are situated in frequency limiting paths

The adder must:

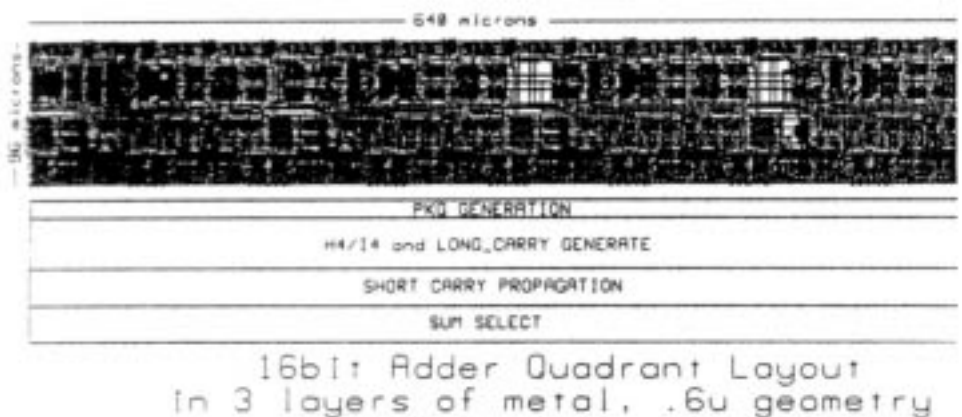
- Be as fast as possible
- Be area efficient
- Be compatible with reliability and composition goals of the rest of the processor

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## Key Features of the Adder Design

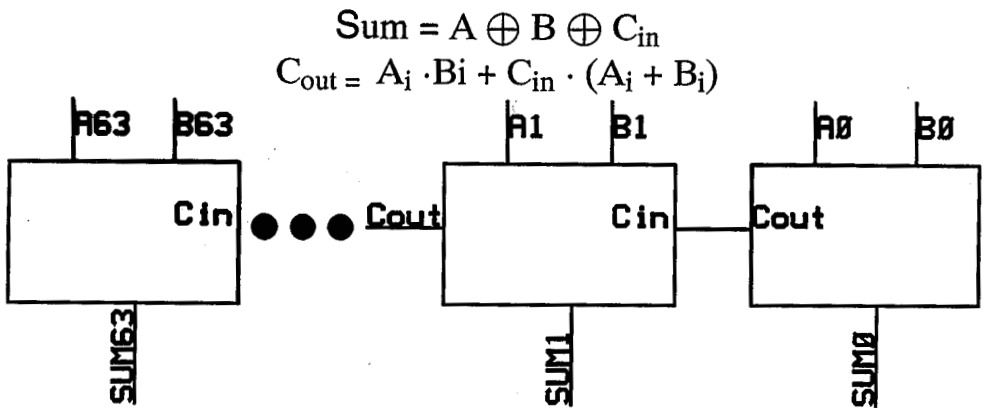
- Dual rail dynamic logic
  - ▶ Fastest logic family for this CMOS technology
  - ▶ Enables seamless interface to both dynamic and static logic downstream
- Distributed carry chain and logical reductions enable a dense layout
- Use of Ling's equations in dynamic CMOS enable a 4 gate delay 64b add

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## Adder Design



Problem: Carry ripple from LSB to MSB for a 64 bit adder requires 65 gate delays.

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## Speeding Up Addition

- Carry look ahead and sum select techniques
- Ling's equations
- Fast circuit techniques
  - ▶ Pass gate logic
  - ▶ Low voltage swing
  - ▶ Bipolar (BiCMOS) logic
  - ▶ Dynamic CMOS

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## Carry Lookahead Techniques

Calculate groups of carries (in our case, 4 at a time) in parallel to reduce the carry calculation time to  $2 \cdot \log_r[n] + 2$  gate delays for fanin 4 gates.

$r$  = group size,  $n$  = number of bits to add

$$C_2 = G_1 + G_0 \cdot P_0$$

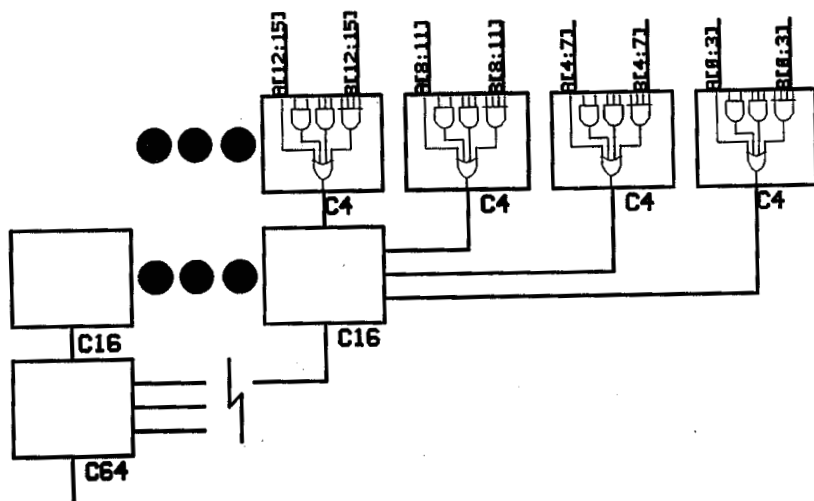
$$C_4 = G_3 + G_2 \cdot P_3 + G_1 \cdot P_2 \cdot P_3 + G_0 \cdot P_1 \cdot P_2 \cdot P_3$$

A	B	P	G	K
0	0	0	0	1
0	1	1	0	0
1	0	1	0	0
1	1	0 or 1	1	0

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## Carry Lookahead Techniques

These group carries are combined at another level to produce a long carry and so on.



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## Sum Select

- Calculate two sums per block, one with LSB carryin of 0, another with carryin of 1
- When the long carry comes, select the correct sum.

Total gate delays for CLA/sum select group of 4:

$$1 + 2 \cdot \log_4[64] + 1 = 8 \text{ gate delays}$$

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## Using Ling's Equations

- Define a group of 4 "psuedo-carry"

$$H_4 = G_3 + G_2 \cdot P_2 + G_1 \cdot P_1 \cdot P_2 + G_0 \cdot P_2 \cdot P_1 \cdot P_0$$

vs.

$$C_4 = G_3 + G_2 \cdot P_3 + G_1 \cdot P_2 \cdot P_3 + G_0 \cdot P_3 \cdot P_2 \cdot P_1$$

- $C_4 = H_4 \cdot P_3$

Continued...

## Using Ling's Equations

Why is the  $H_4$  equation a good thing?

- If  $P_x = A_x + B_x$ , then  $G_x \Rightarrow P_x$
- Use this reduction to define  $H_4$  in terms of the input operands, not P and G

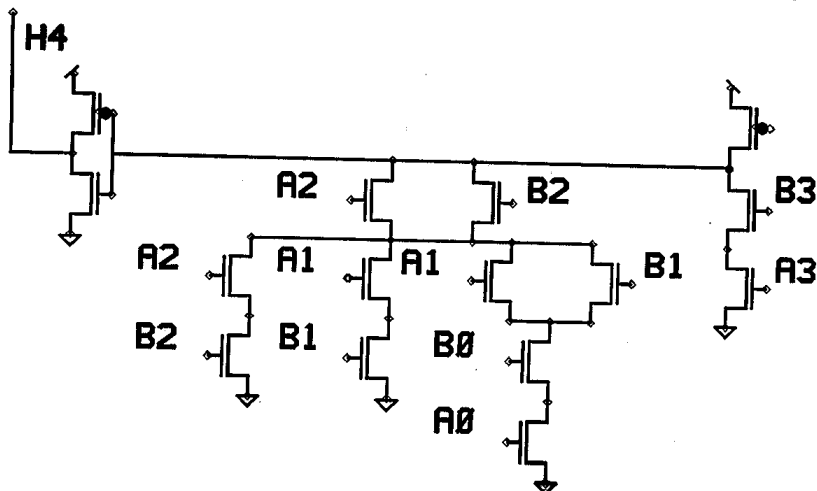
$$H_4 = A_3B_3 + A_2B_2 + A_2A_1B_1 + B_2A_1B_1 + A_2A_1A_0B_0 + A_2B_1A_0B_0 + B_2A_1A_0B_0 + B_2B_1A_0B_0$$

Calculate  $H_4$  in **8 terms, fanin of 4** vs. **15 terms fanin 5** for a similarly flattened  $C_4$ , or **one gate delay** vs. **three**

Continued...

## Using Ling's Equations

$$H_4 = A_3B_3 + A_2B_2 + A_2A_1B_1 + B_2A_1B_1 + A_2A_1A_0B_0 + A_2B_1A_0B_0 + B_2A_1A_0B_0 + B_2B_1A_0B_0$$



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## Using Ling's Equations

A fast group of 4 propagate is also necessary to combine for the next level (16) of carry generate:

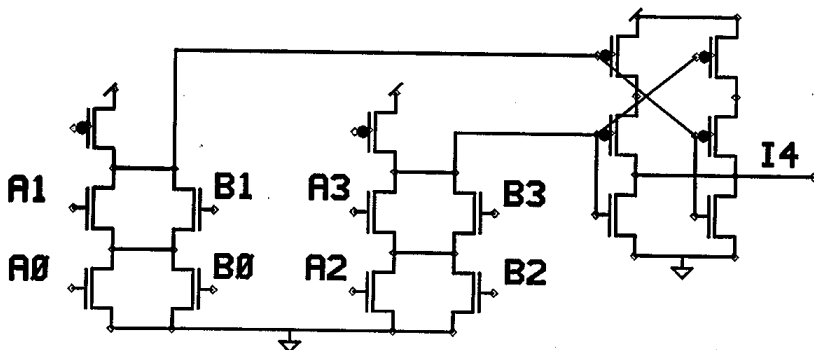
$$I_4 = P_0 P_1 P_2 P_3$$

If  $P = A + B$ , this can be done in one gate delay using "wired-or" techniques also.

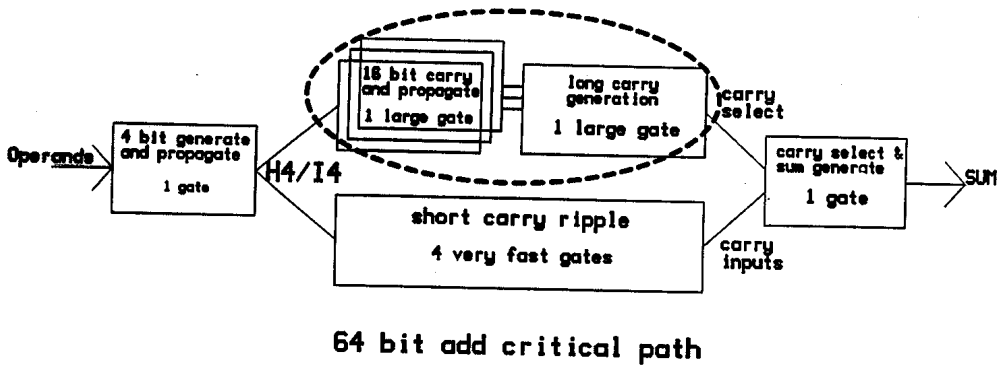
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## Using Ling's Equations

$$I_4 = P_0 P_1 P_2 P_3$$



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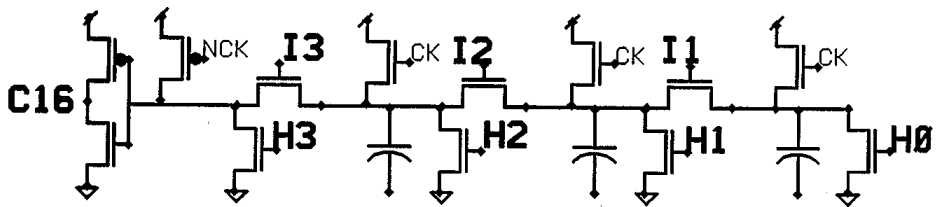
## Long Carry Propagate

Combine  $I_4$  and  $H_4$  to produce  $C_{16}$

- As fast as possible since this is directly in the critical path
- Minimum area
- Minimum wires
- ▶ Use a combination of Dynamic, Pass gate, and Low Voltage techniques to optimize for these three parameters

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$$C_{16} = H_3 + H_2 \cdot I_3 + H_1 \cdot I_2 \cdot I_3 + H_0 \cdot I_1 \cdot I_2 \cdot I_3$$

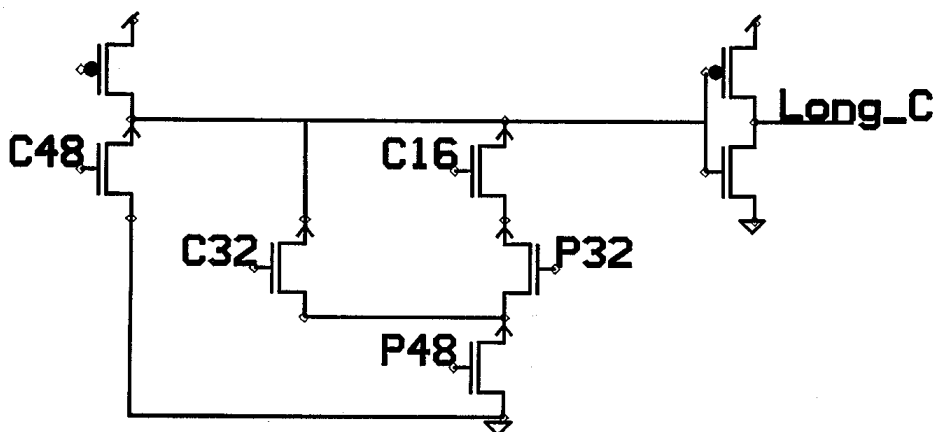


### Long Carry Propagate

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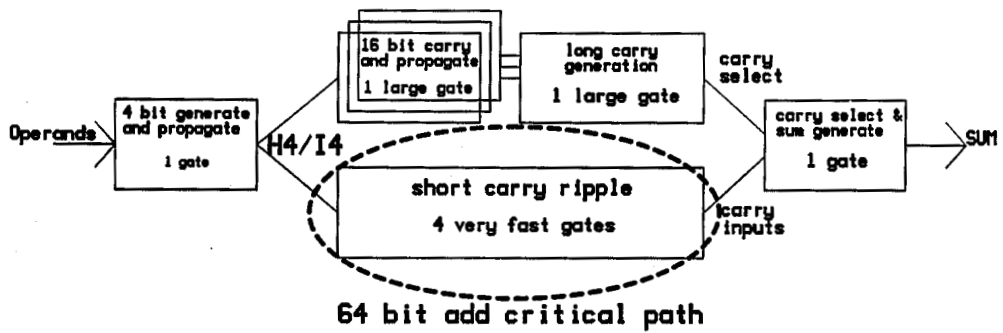
Combine group of 16 carries for final long carry:

$$\text{Long\_C} = C_{48} + C_{32} \cdot P_{48} + C_{16} \cdot P_{32} \cdot P_{48}$$



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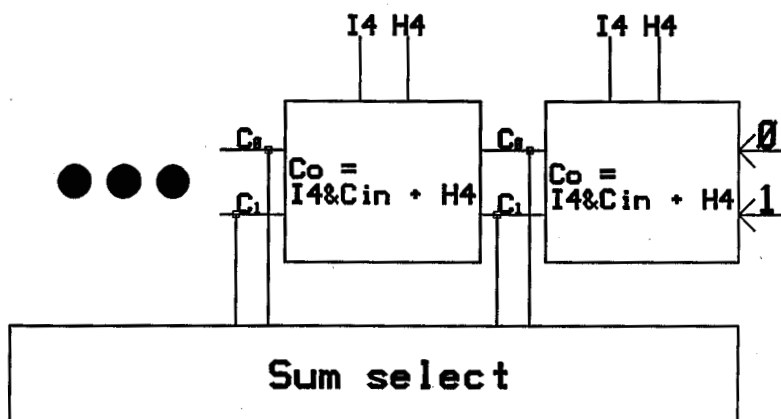


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**Both flavors of Local Carry must be generated**

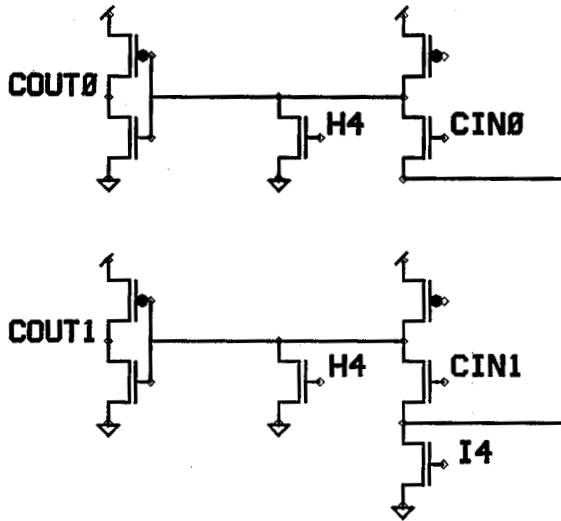
- Before the long carry arrives
- In very little area due to high replication factor



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## Short Carry Generate

Use a by-four scheme  $C_o = I_4 \cdot C_{in} + H_4$

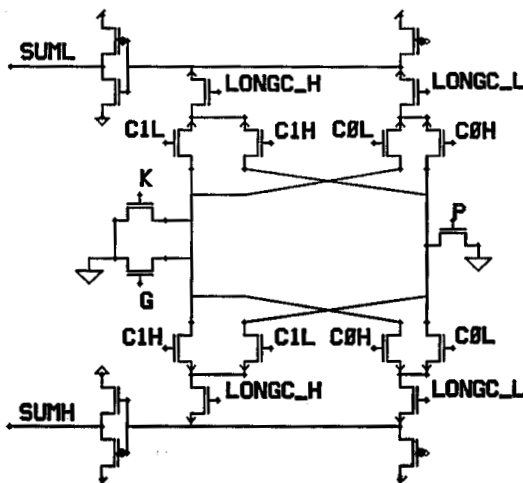


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## Sum Generate and Select

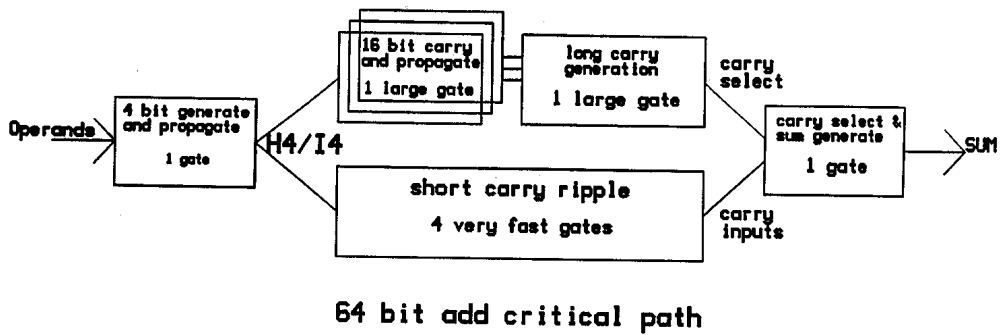
$$\text{Sum} = A \oplus B \oplus C_{in}$$

$C_{in}$  is selected from  $C_0$  or  $C_1$  by  $C_{long}$

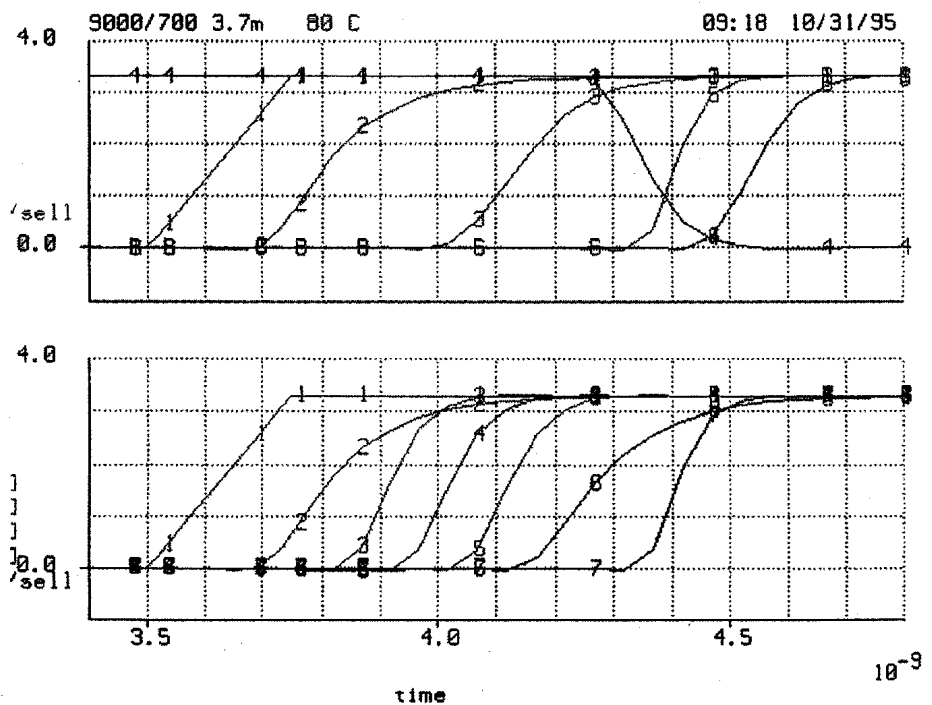


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## Summary



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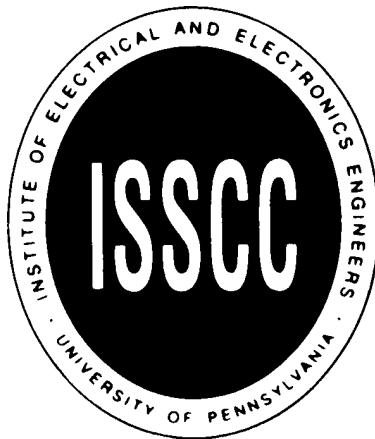
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## **Performance Analysis**

- SPICE analysis indicates that the delay from operands to sum is **.930 nanoseconds** under Nominal voltage (3.3), Nominal FETs, 80C
- Silicon confirms simulated speed based on characterization of numerous paths involving the adder

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**Source**

1996 IEEE International Solid-State Circuits Conference  
1996 Slide Supplement, pp. 290-291